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Type: **Poster Presentation**

## Diffusion studies of Xenon and Krypton implanted in CVD-SiC

*Thursday, 12 July 2012 17:30 (2 hours)*

### Abstract content **<br>** **&nbsp;**; (Max 300 words)

The diffusion behaviour of implanted xenon and Krypton in CVD-SiC has been investigated using Rutherford backscattering spectroscopy (RBS) and Scanning electron microscopy (SEM) techniques. Xenon (Xe<sup>+</sup>) and Krypton ions with an energy of 360 KeV were implanted in SiC to a fluence of  $2 \times 10^{16}$  cm<sup>-2</sup> at room temperature (23°C), 350°C and 600°C. Sequential annealing was performed from 1000°C to 1500°C in 100°C. By comparing the widths of the as implanted profiles to the after annealing profiles the diffusion coefficients was determined while the changes in samples surfaces were monitored by SEM.

### Apply to be **<br>** consider for a student **<br>** **&nbsp;**; award (Yes / No)?

no

### Level for award **<br>**; (Hons, MSc, **<br>** **&nbsp;**; PhD)?

na

### Main supervisor (name and email) **<br>** and his / her institution

no

### Would you like to **<br>** submit a short paper **<br>** for the Conference **<br>** Proceedings (Yes / No)?

no

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**Session Classification:** Poster Session

**Track Classification:** Track A - Division for Condensed Matter Physics and Materials